

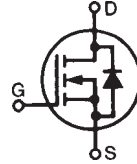
**TrenchT2™ HiperFET™**  
**Power MOSFET**
**IXFH400N075T2**  
**IXFT400N075T2**

$$V_{DSS} = 75V$$

$$I_{D25} = 400A$$

$$R_{DS(on)} \leq 2.3m\Omega$$

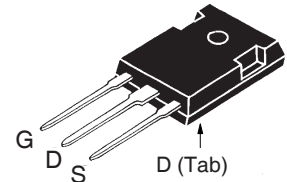
N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode



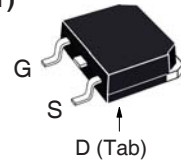
Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $175^\circ C$	75	V
$V_{DGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$	75	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$ (Chip Capability)	400	A
$I_{LRMS}$	Lead Current Limit, RMS	160	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	1000	A
$I_A$	$T_C = 25^\circ C$	200	A
$E_{AS}$	$T_C = 25^\circ C$	1.5	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 175^\circ C$	15	V/ns
$P_D$	$T_C = 25^\circ C$	1000	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	1.6mm (0.062in.) from Case for 10s	300	$^\circ C$
$T_{sold}$	Plastic Body for 10 seconds	260	$^\circ C$
$M_d$	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	75		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.0		V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 150^\circ C$			25 $\mu A$
				1.5 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 100A$ , Notes 1 & 2			2.3 m $\Omega$

TO-247 (IXFH)



TO-268 (IXFT)



G = Gate      D = Drain  
 S = Source    Tab = Drain

**Features**

- International Standard Packages
- 175 $^\circ C$  Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Fast Intrinsic Diode
- Low  $R_{DS(on)}$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- DC/DC Converters and Off-line UPS
- Primary- Side Switch
- High Current Switching Applications

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1	80	130	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		24	nF
$C_{oss}$		2770	pF	
$C_{rss}$		455	pF	
$R_{Gi}$	Gate Input Resistance		1.33	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 200\text{A}$ $R_G = 1\Omega$ (External)		35	ns
$t_r$		20	ns	
$t_{d(off)}$		67	ns	
$t_f$		44	ns	
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		420	nC
$Q_{gs}$		114	nC	
$Q_{gd}$		130	nC	
$R_{thJC}$				$0.15^\circ\text{C/W}$
$R_{thCH}$	TO-247	0.21		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			400 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			1200 A
$V_{SD}$	$I_F = 100\text{A}, V_{GS} = 0\text{V}$ , Note 1			1.2 V
$t_{rr}$	$I_F = 100\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 37.5\text{V}$		77	ns
$I_{RM}$		5.4	A	
$Q_{RM}$		210	nC	

### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Includes lead resistance.

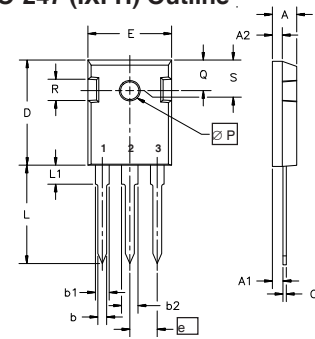
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

### IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

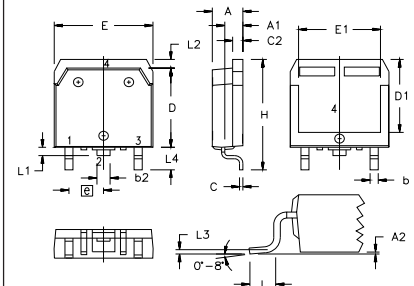
### TO-247 (IXFH) Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

### TO-268 (IXFT) Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

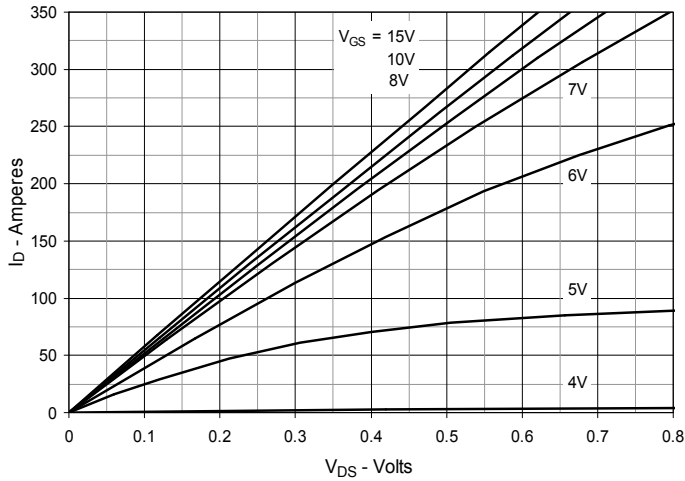


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

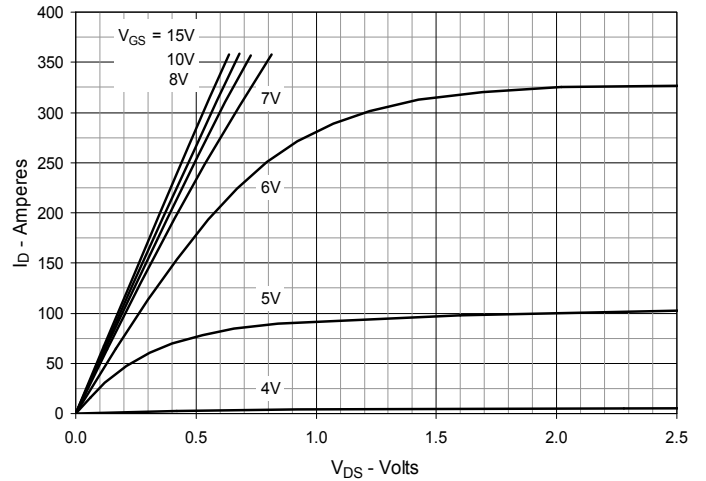


Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$

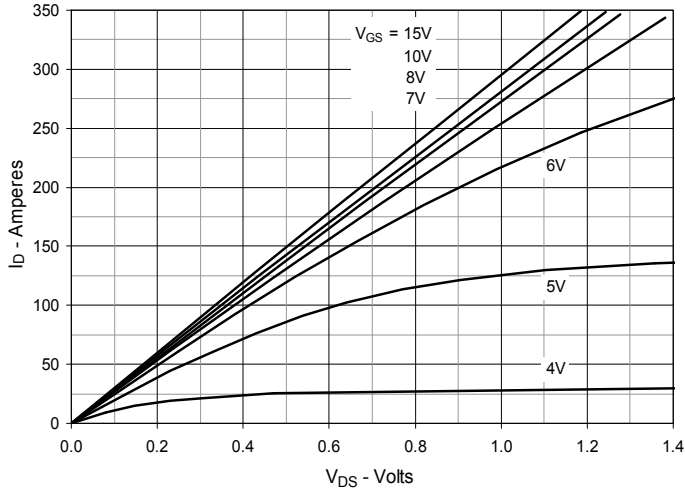


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 200\text{A}$  Value vs. Junction Temperature

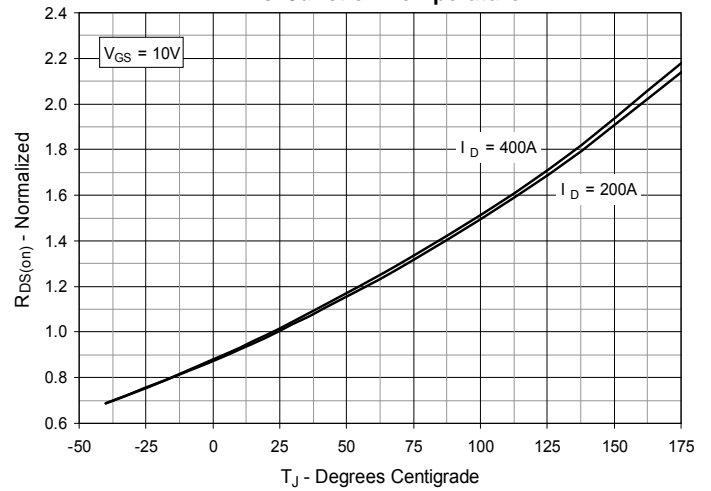


Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 200\text{A}$  vs. Drain Current

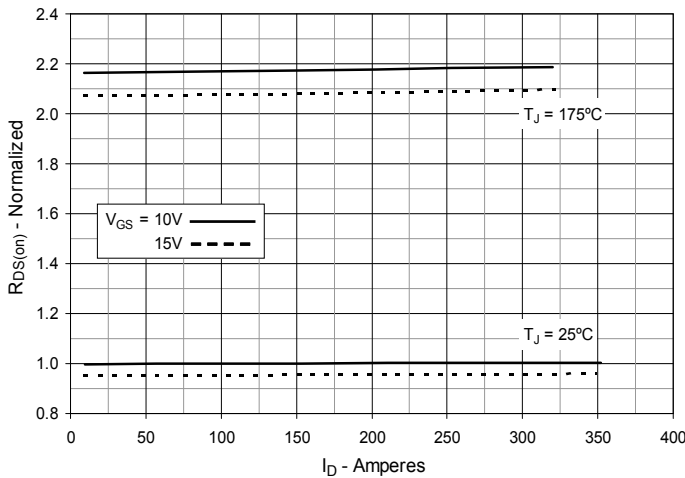
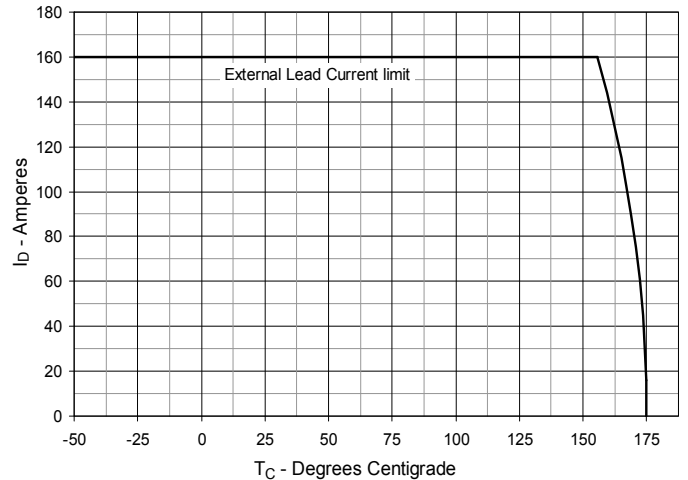
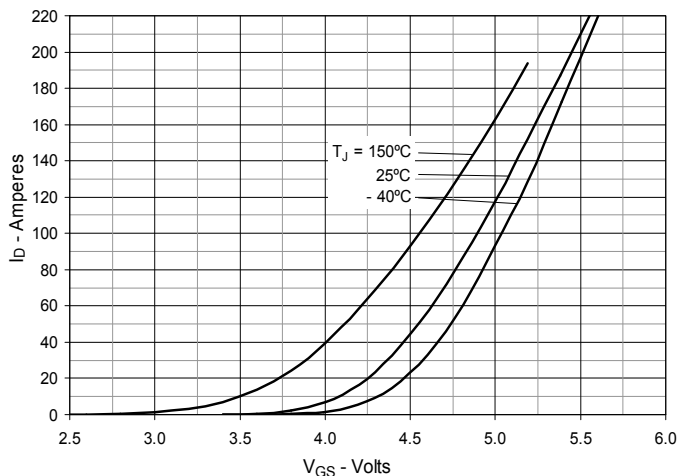


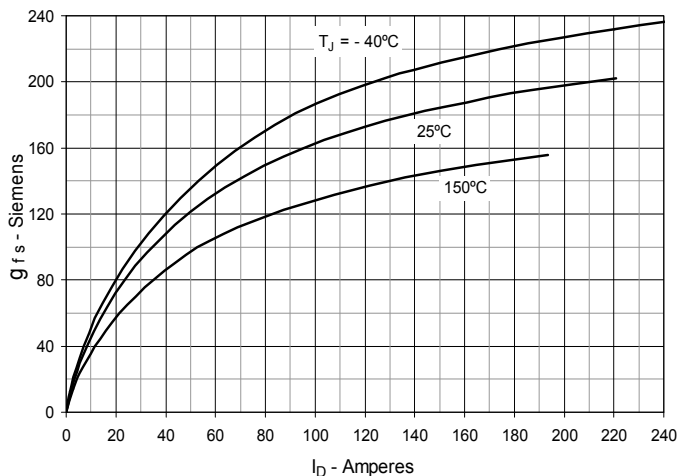
Fig. 6. Drain Current vs. Case Temperature



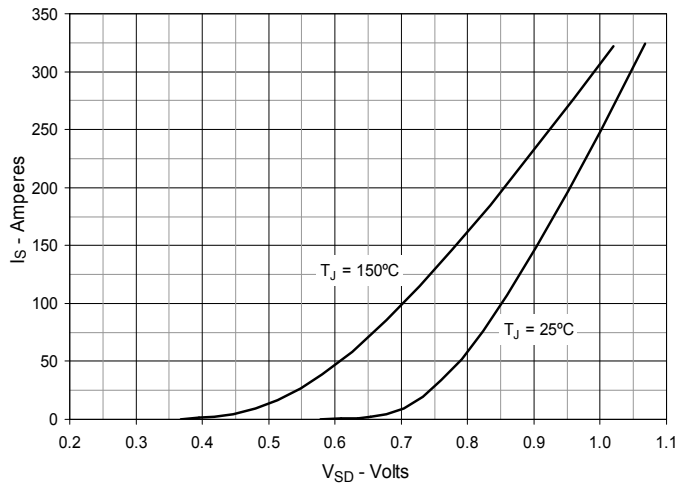
**Fig. 7. Input Admittance**



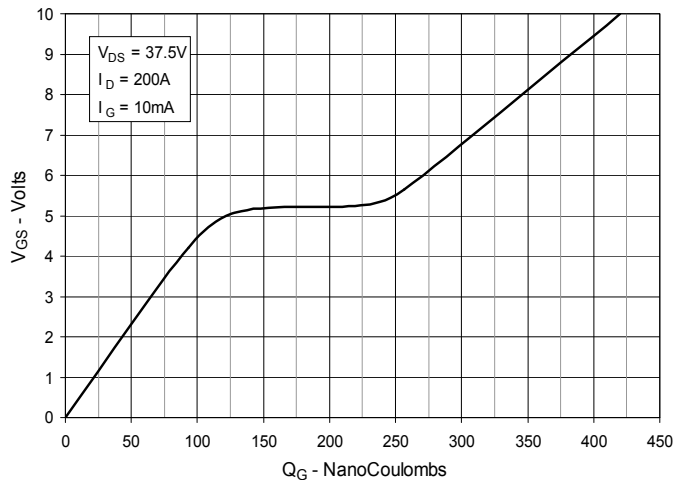
**Fig. 8. Transconductance**



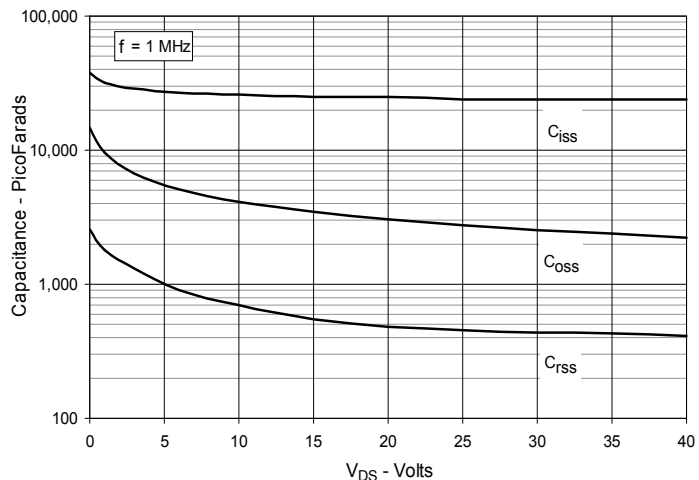
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



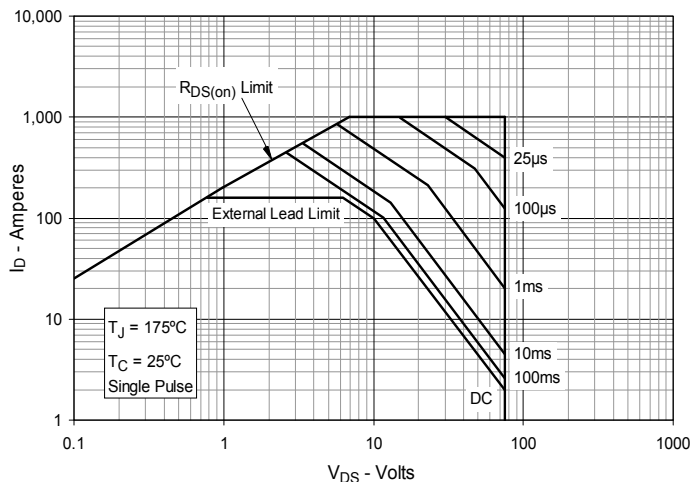
**Fig. 10. Gate Charge**



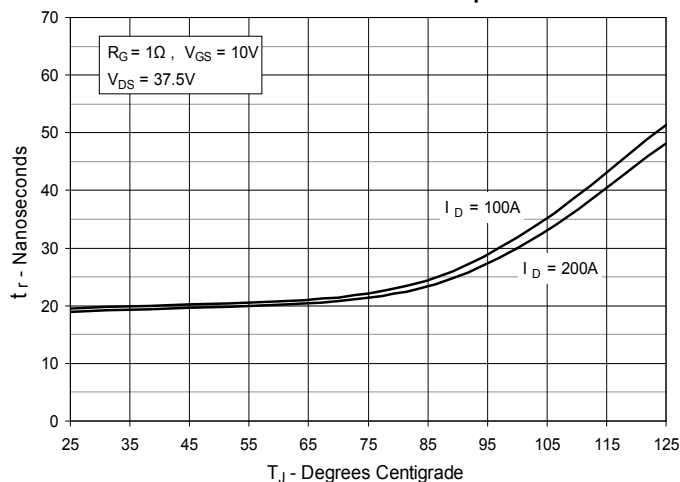
**Fig. 11. Capacitance**



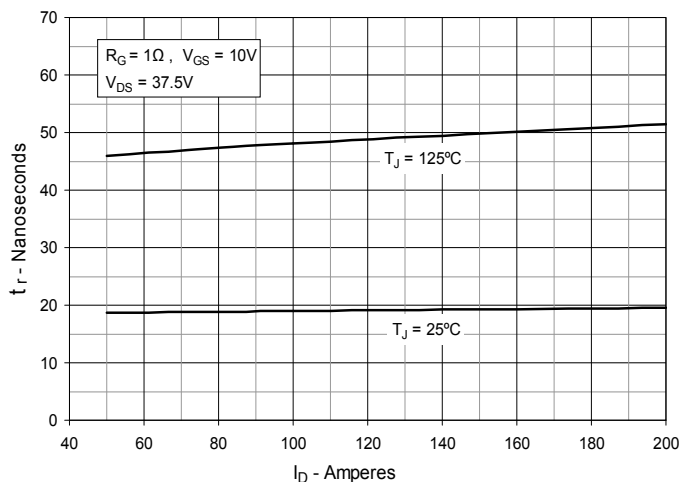
**Fig. 12. Forward-Bias Safe Operating Area**



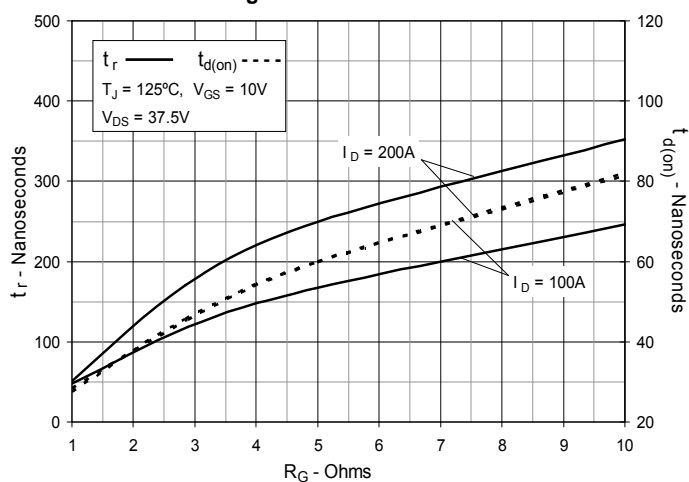
**Fig. 13. Resistive Turn-on  
Rise Time vs. Junction Temperature**



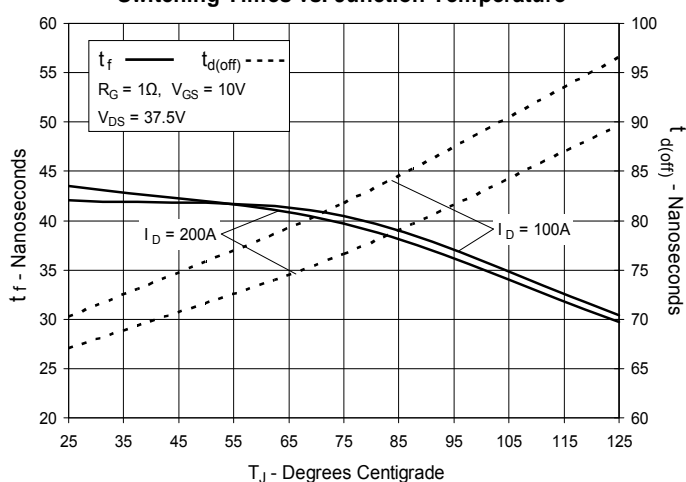
**Fig. 14. Resistive Turn-on  
Rise Time vs. Drain Current**



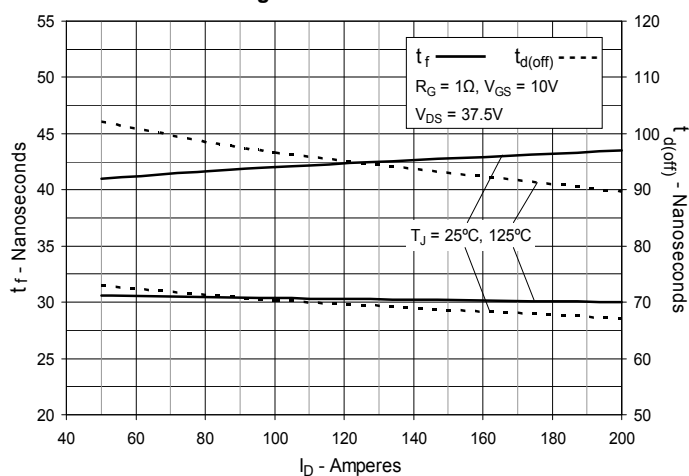
**Fig. 15. Resistive Turn-on  
Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off  
Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off  
Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off  
Switching Times vs. Gate Resistance**

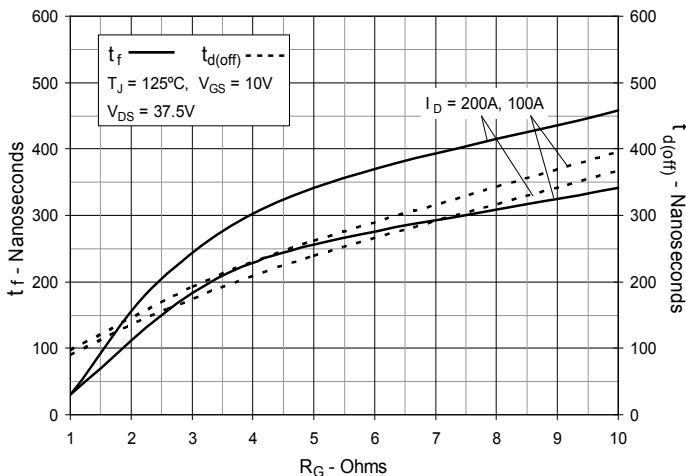


Fig. 19. Maximum Transient Thermal Impedance

